

ISC Silicon NPN RF Transistor

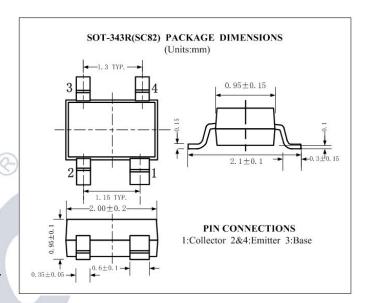
BFP196W

DESCRIPTION

- Low Noise Figure
 NF = 1.3 dB TYP.
 @V_{CE} = 6 V, I_C = 5 mA, f = 1GHz
- High Gain $| S_{21} |^2 = 18 dB TYP.$ $@V_{CE} = 6 \ V,I_C = 30 \ mA,f = 1 GHz$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for use in low noise ,high-gain amplifiers and linear broadband amplifiers.



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	2	V
Ic	Collector Current-Continuous	100	mA
Pc	Collector Power Dissipation @Tc=25°C	700	mW
TJ	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

isc website: www.iscsemi.com

isc & iscsemi is registered trademark



ISC Silicon NPN RF Transistor

BFP196W

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA ; I _B = 0	12			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 10V; I _E = 0			100	nA
h _{FE}	DC Current Gain	I _C = 30mA ; V _{CE} = 6V	50	100	250	
f⊤	Current-Gain—Bandwidth Product	I _C = 30mA ; V _{CE} = 8V	8.5	9		GHz
Cre	Feedback Capacitance	I _E = 0 ; V _{CB} = 6V; f= 1MHz		0.4		pF
Се	Emitter capacitance	IC=iC=0; VEB=0.5V; f=1MHz		1.5		pF
Cc	Collector capacitance	IE=ie=0; Vcb=8V; f=1MHz		0.6		pF
S ₂₁ ²	Insertion Power Gain	I _C = 30mA ; V _{CE} = 6V; f= 1GHz	17	18		dB
NF	Noise Figure	I _C = 5mA ; V _{CE} = 6V; f= 1GHz		1.3		dB
		I _C = 5mA ; V _{CE} = 6V; f= 2GHz		2.0		

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com

² isc & iscsemi is registered trademark